

DATA SHEET

BSP206

P-channel enhancement mode
vertical D-MOS transistor

Product specification
File under Discrete Semiconductors, SC13B

April 1995

P-channel enhancement mode vertical D-MOS transistor

BSP206

DESCRIPTION

P-channel enhancement mode vertical D-MOS transistor in a miniature SOT223 envelope and intended for use in relay, high-speed and line-transformer drivers.

QUICK REFERENCE DATA

Drain-source voltage	$-V_{DS}$	max.	60 V
Drain current (DC)	$-I_D$	max.	350 mA
Drain-source ON-resistance $-I_D = 200 \text{ mA}; -V_{GS} = 10 \text{ V}$	$R_{DS(on)}$	max.	6 Ω
Gate threshold voltage	$-V_{GS(th)}$	max.	3.5 V

FEATURES

- Very low $R_{DS(on)}$
- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No secondary breakdown

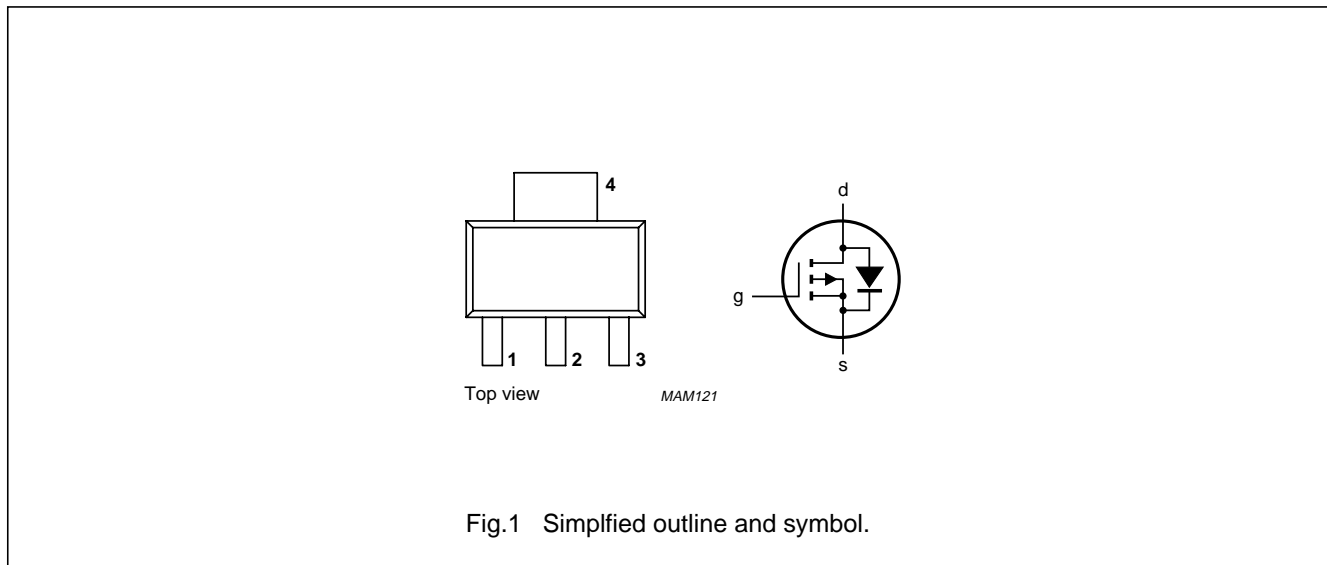
PINNING - SOT223

- 1 = gate
- 2 = drain
- 3 = source
- 4 = drain

Marking code

BSP206

PIN CONFIGURATION



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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	$-V_{DS}$	max.	60 V
Gate-source voltage (open drain)	$\pm V_{GSO}$	max.	20 V
Drain current (DC)	$-I_D$	max.	350 mA
Drain current (peak)	$-I_{DM}$	max.	700 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$ (note 1)	P_{tot}	max.	1.5 W
Storage temperature range	T_{stg}		-65 to + 150 $^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient (note 1)	$R_{th\ j-a}$	=	83.3 K/W
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Note

1. Device mounted on an epoxy printed-circuit board 40 mm × 40 mm × 1.5 mm; mounting pad for the drain lead min. 6 cm².

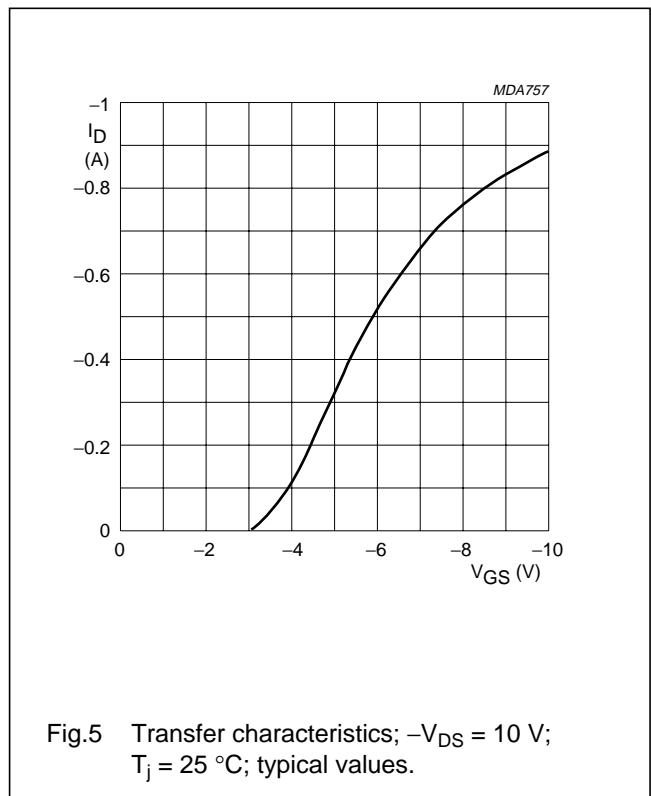
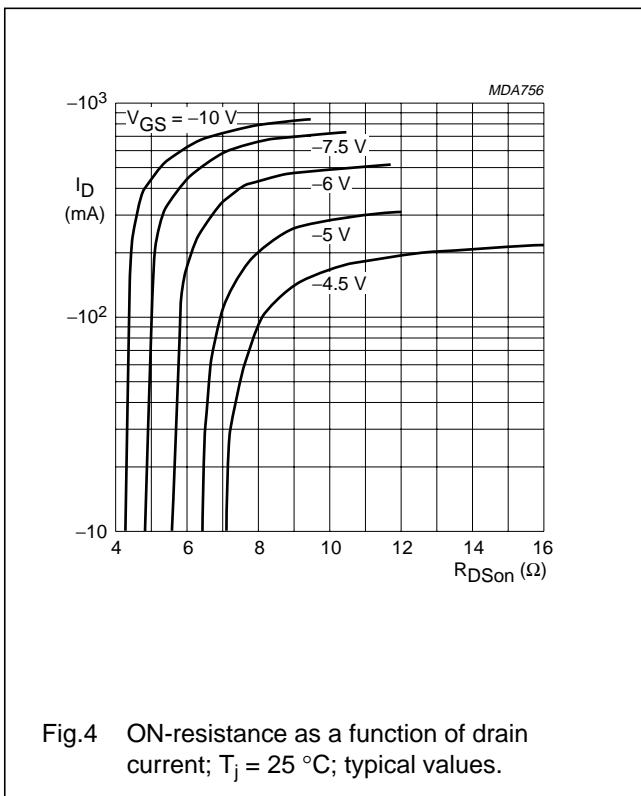
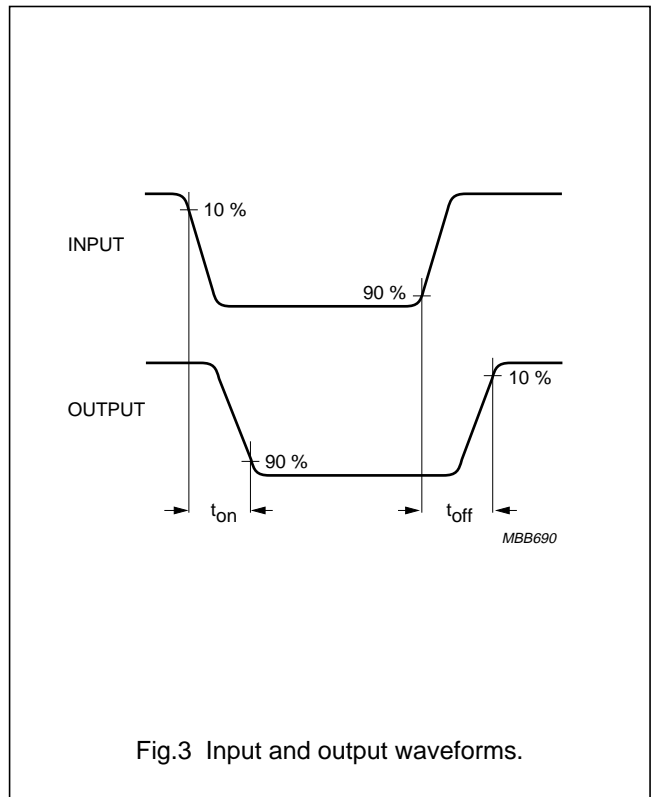
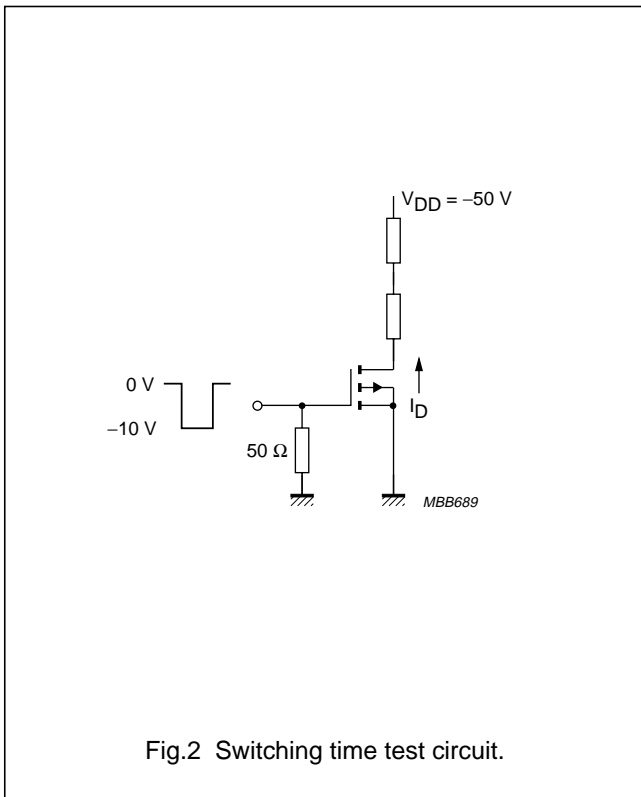
CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Drain-source breakdown voltage $-I_D = 10\text{ }\mu\text{A}; V_{GS} = 0$	$-V_{(BR)DSS}$	min.	60 V
Drain-source leakage current $-V_{DS} = 48\text{ V}; V_{GS} = 0$	$-I_{DSS}$	max.	1.0 μA
Gate-source leakage current $\pm V_{GS} = 20\text{ V}; V_{DS} = 0$	$\pm I_{GSS}$	max.	100 nA
Gate threshold voltage $-I_D = 1\text{ mA}; V_{DS} = V_{GS}$	$-V_{GS(th)}$	min. max.	1.5 V 3.5 V
Drain-source ON-resistance $-I_D = 200\text{ mA}; -V_{GS} = 10\text{ V}$	$R_{DS(on)}$	typ. max.	4.5 Ω 6 Ω
Transfer admittance $-I_D = 200\text{ mA}; -V_{DS} = 15\text{ V}$	$ Y_{fs} $	min. typ.	100 mS 200 mS
Input capacitance at $f = 1\text{ MHz};$ $-V_{DS} = 10\text{ V}; V_{GS} = 0$	C_{iss}	typ. max.	55 pF 70 pF
Output capacitance at $f = 1\text{ MHz};$ $-V_{DS} = 10\text{ V}; V_{GS} = 0$	C_{oss}	typ. max.	30 pF 45 pF
Feedback capacitance at $f = 1\text{ MHz};$ $-V_{DS} = 10\text{ V}; V_{GS} = 0$	C_{rss}	typ. max.	8 pF 12 pF
Switching times (see Figs 2 and 3) $-I_D = 200\text{ mA}; -V_{DD} = 50\text{ V};$ $-V_{GS} = 0\text{ to }10\text{ V}$	t_{on}	typ. max.	4 ns 8 ns
	t_{off}	typ. max.	15 ns 25 ns

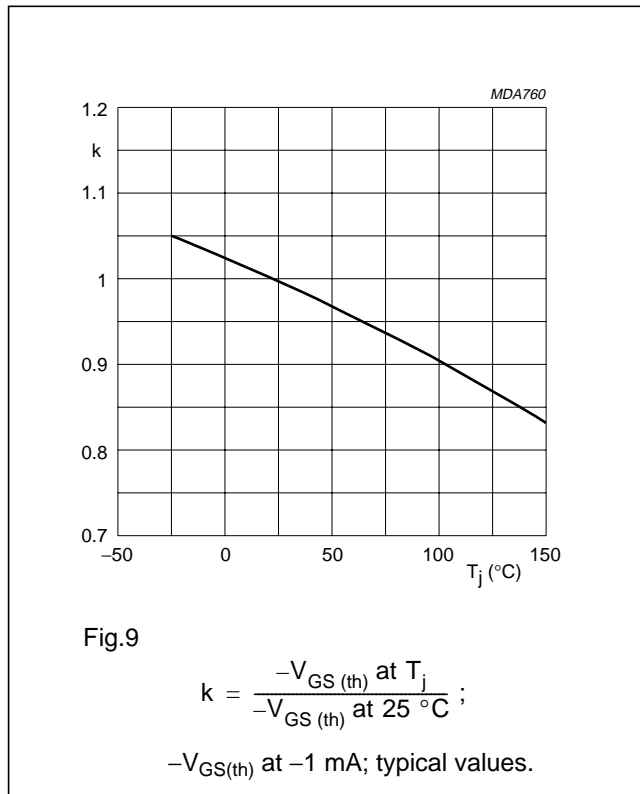
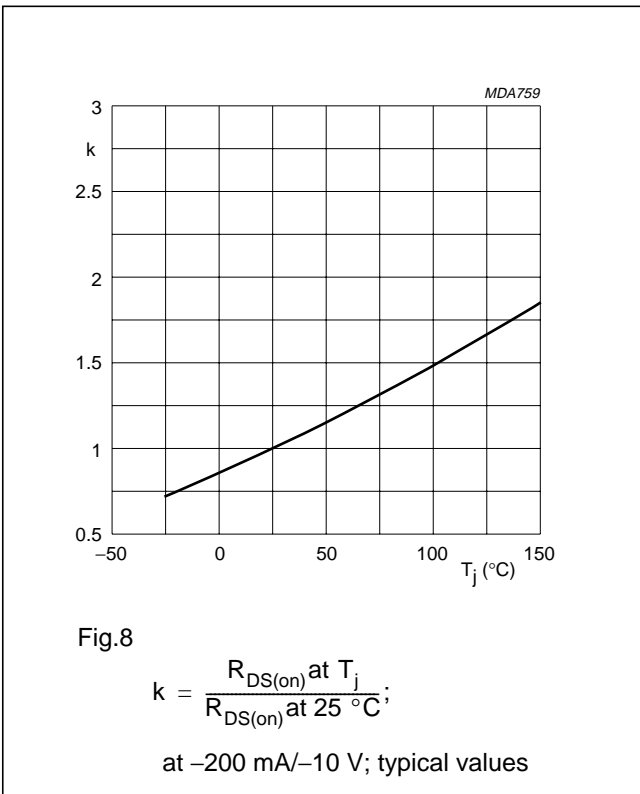
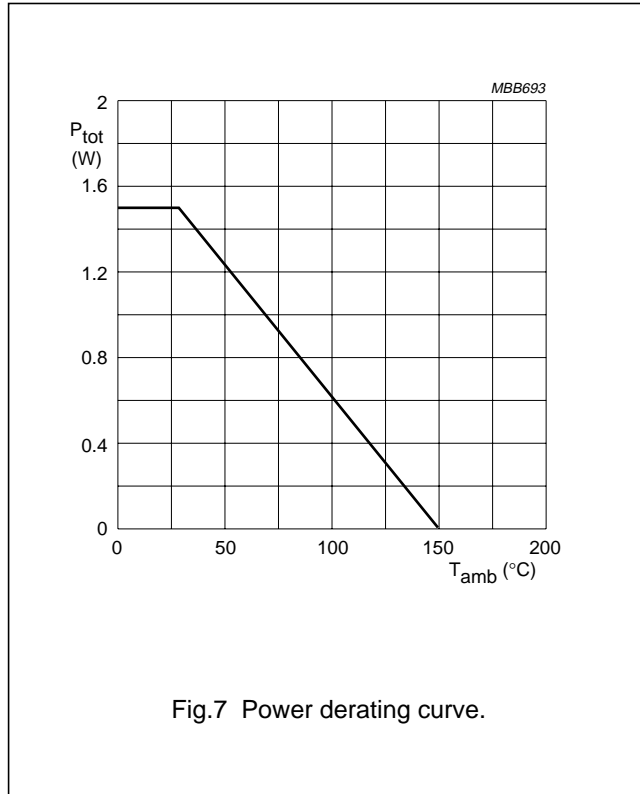
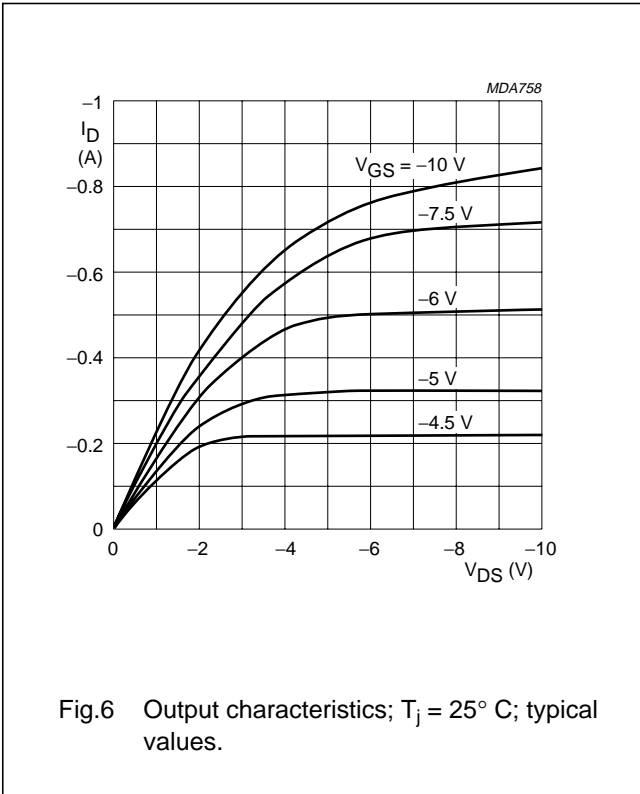
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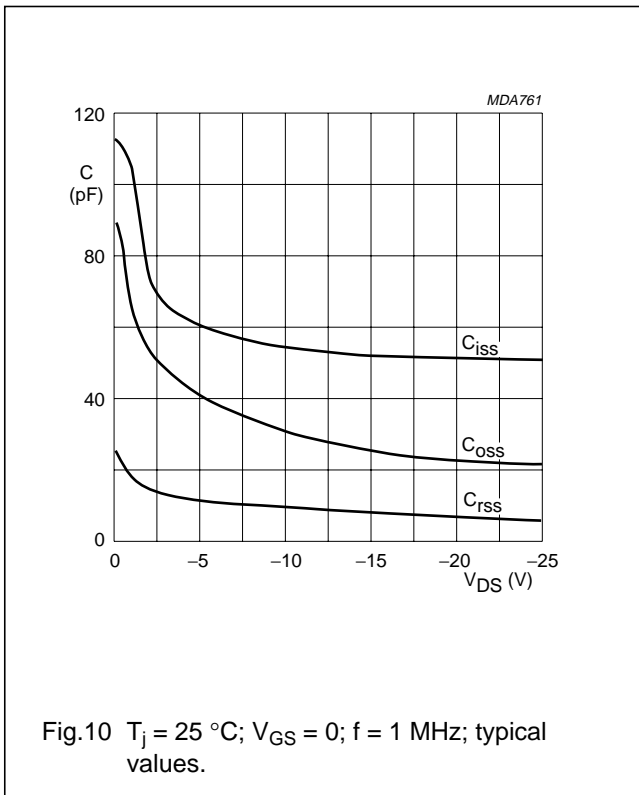
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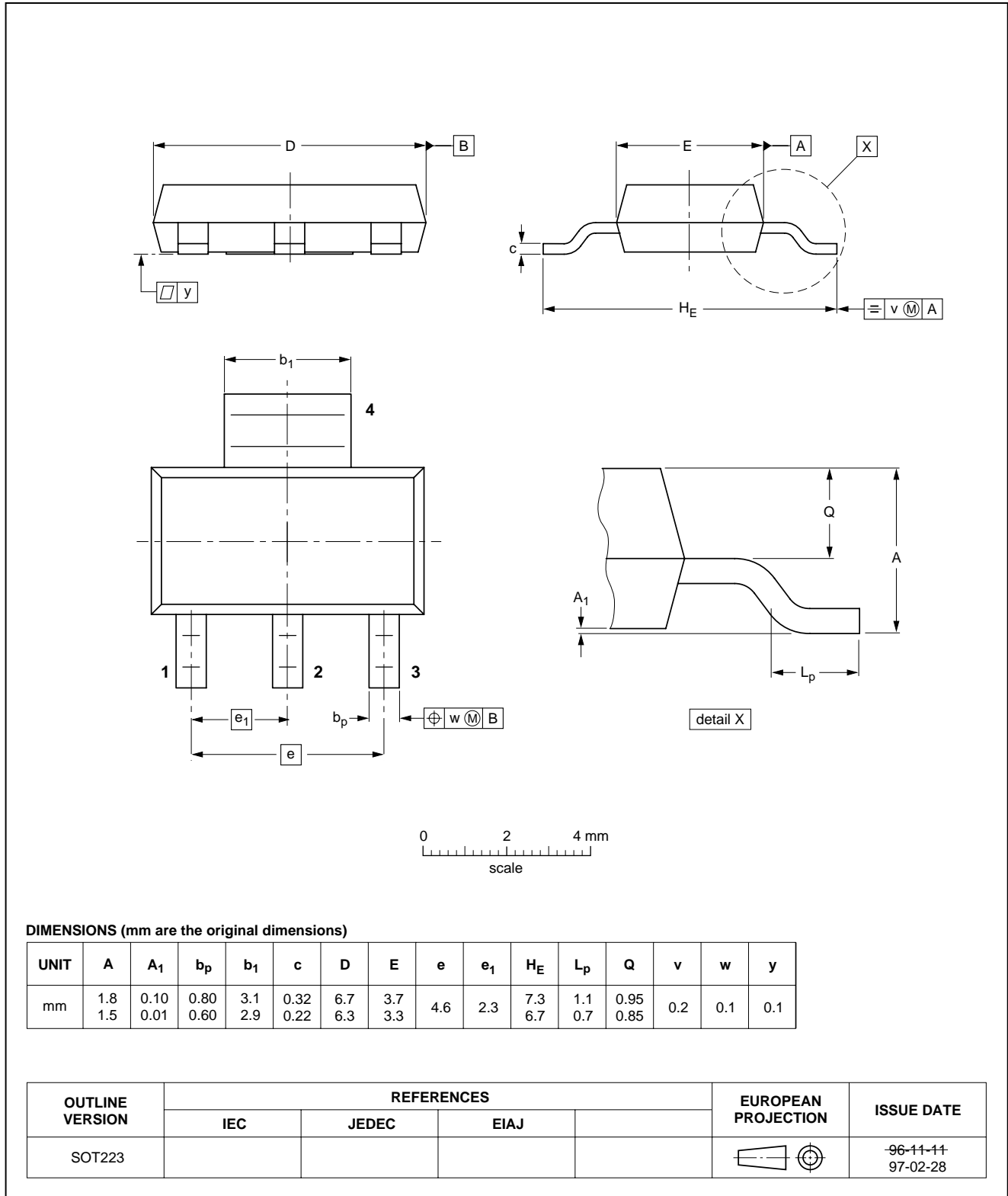
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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



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BSP206**DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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NOTES

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